

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (Canceled).

Claim 2 (Currently Amended): ~~Method~~ The method as recited in claim ~~1~~ 12, wherein an adhesive material is used for the attachment layer.

Claim 3 (Currently Amended): ~~Method~~ The method as recited in claim 2, wherein an adhesive material having a lower adhesion to the front face surface of the wafer at a higher temperature is used.

Claim 4 (Currently Amended): ~~Method~~ The method as recited in claim 2 wherein ~~the individual release of the semiconductor circuits are individually released from the carrier is performed mechanically, by overcoming the adhesion force of the attachment material layer to the front face surface of the wafer.~~

Claim 5 (Currently Amended): ~~Method~~ The method as recited in claim ~~±~~ 12, wherein the substrate is reduced in thickness to a thickness of less than 100 μm .

Claim 6 (Currently Amended): ~~Method~~ The method as recited in claim ~~±~~ 12, wherein the separating trenches are produced by means of a photolithographic etching process.

Claims 7-8 (Canceled).

Claim 9 (Currently Amended): ~~Method~~ The method as recited in claim ~~±~~ 12, wherein the ~~deposition of~~ back face metallization is ~~performed~~ deposited after production of the separating trenches.

Claim 10 (Currently Amended): ~~Method~~ The method as recited in claim 6, wherein a common photolithographic mask is used for the production of the passage holes and the separating trenches.

Claim 11 (Currently Amended). ~~Method~~ The method as recited in claim ~~±~~ 12, wherein an electrical function test of the semiconductor circuits is performed after separation.

Claim 12 (New): A method for producing individual monolithically integrated semiconductor circuit arrangements from a wafer composite substrate comprising the following steps:

- (a) forming a plurality of separate component structures comprising monolithic semiconductor circuits and conductive surfaces on a front face surface of a wafer;
- (b) covering the front face surface of the wafer with a protective layer to form a wafer composite substrate;
- (c) attaching the wafer to a support via an attachment layer applied over the support;
- (d) reducing the substrate to a selected thickness;
- (e) producing passage holes through the substrate up to the conductive surfaces on the front face surface;
- (f) producing separating trenches between the monolithic semiconductor circuits up to or into the attachment layer, including removal of the protective layer under the separating trenches and lateral under-etching of the substrate;

(g) depositing a back face metallization on a back face of the substrate and forming electrical connections through the passage holes; and

(h) individually releasing the semiconductor circuits from the support for further individual processing.